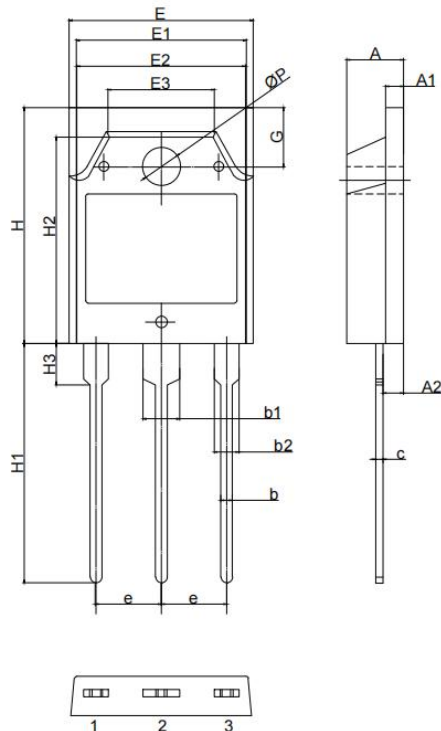
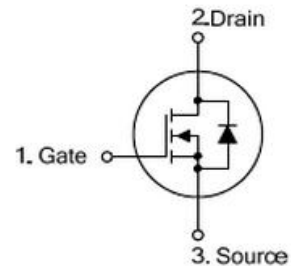
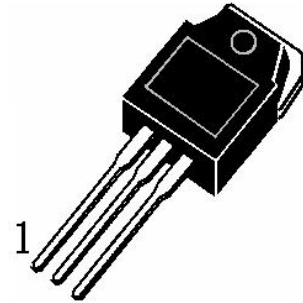


**650V super-junction Power MOSFET**
**◆ Features:**

- ◇ Very Low FOM RDS(on)  
低内阻
- ◇ %100 avalanche tested  
%100 雪崩能量测试
- ◇ RoHS compliant  
RoHS 认证
- ◇ Improved dv/dt capability, high ruggedness  
提高 dv/dt 能力, 高耐用性

**◆ Applications**

- ◇ High efficiency switch mode power supplies  
高效率开关电源
- ◇ Power factor correction  
功率因数校正
- ◇ Electronic lamp ballast  
电子整流器


**TO-3PNB**


TO-3PNB尺寸表/mm			
Symbol	Min	Nom	Max
A	4.60	4.80	5.00
A1	1.30	1.50	1.60
A2	1.40	1.50	1.60
b	0.80	1.00	1.20
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.20	15.60	16.00
E1	13.20	13.40	13.60
E2	13.10	13.50	13.50
E3	9.10	9.30	9.50
H	19.80	20.00	20.20
H1	20.10	20.30	20.50
H2	18.50	18.70	18.90
H3	3.20	3.50	3.80
G	4.80	5.00	5.20
ØP	3.00	3.20	3.40

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
V <sub>DSS</sub>	Drain-Source Voltage 漏源电压	650	V
V <sub>GS</sub>	Gate-Source Voltage-Continuous 栅源电压	±30	V
I <sub>D</sub>	Drain Current-Continuous (Note 2) 漏极持续电流	53	A
I <sub>DM</sub>	Drain Current-Single Plused (Note 1) 漏极单次脉冲电流	212	A
P <sub>D</sub>	Power Dissipation (Note 2) 功率损耗	385	W
T <sub>j</sub>	Max.Operating junction temperature 最大结温	150	°C

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbo l	Parameters	Min	Typ	Max	Units	Conditions
<b>Static Characteristics</b>						
B <sub>VDSS</sub>	Drain-Source Breakdown VoltageCurrent (Note 1) 漏极击穿电压	650	--	--	V	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C
V <sub>GS(th)</sub>	Gate Threshold Voltage 栅极开启电压	3.0	--	5.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
R <sub>DS(on)</sub>	Drain-Source On-Resistance 漏源导通电阻	--	0.065	0.067	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =26.5A
I <sub>GSS</sub>	Gate-Body Leakage Current 栅极漏电流	--	--	±100	nA	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0
I <sub>DSS</sub>	Zero Gate Voltage Drain Current 零栅极电压漏极电流	--	--	11	μA	V <sub>DS</sub> =650V, V <sub>GS</sub> =0
g <sub>fs</sub>	Forward Transconductance 正向跨导	--	38	--	S	V <sub>DS</sub> =40V, I <sub>D</sub> =25A

Switching Characteristics						
$T_{d(on)}$	Turn-On Delay Time 开启延迟时间	--	<b>20.5</b>	--	ns	$V_{DS}=480V$ , $I_D=26.5A$ , $R_G=20\Omega$ (Note 2)
$T_r$	Rise Time 上升时间	--	<b>25</b>	--	ns	
$T_{d(off)}$	Turn-Off Delay Time 关闭延迟时间	--	<b>80</b>	--	ns	
$T_f$	Fall Time 下降时间	--	<b>35</b>	--	ns	
$Q_g$	Total Gate Charge 栅极总电荷	--	<b>20</b>	--	nC	$V_{DS}=480V$ , $V_{GS}=10V$ , $I_D=26.5A$ (Note 2)
$Q_{gs}$	Gate-Source Charge 栅源极电荷	--	<b>25</b>	--	nC	
$Q_{gd}$	Gate-Drain Charge 栅漏极电荷	--	<b>80</b>	--	nC	
Dynamic Characteristics						
$C_{iss}$	Input Capacitance 输入电容	--	<b>4200</b>	--	pF	$V_{DS}=25V$ , $V_{GS}=0$ , $f=1MHz$
$C_{oss}$	Output Capacitance 输出电容	--	<b>95</b>	--	pF	
$C_{rss}$	Reverse Transfer Capacitance 反向传输电容	--	<b>5</b>	--	pF	
$I_S$	Continuous Drain-Source Diode Forward Current (Note 2) 二极管导通正向持续电流	--	--	<b>53</b>	A	
$V_{SD}$	Diode Forward On-Voltage 二极管正向导通电压	--	--	<b>1.2</b>	V	$I_S=26.5A$ , $V_{GS}=0$
$R_{th(j-c)}$	Thermal Resistance, Junction to Case 结到外壳的热阻	--	--	<b>0.32</b>	$^{\circ}C/W$	

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature

Note 2: Pulse test: PW <= 300us , duty cycle <= 2%.